

Appl. No. : 10/624, 728  
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### AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0017] (as amended in the Amendment filed on September 23, 2005) with the following replacement paragraph:

“The dual chamber processing system shown and described herein can include many of the components of the systems shown and described in U.S. Patent Nos. 6,228,773 and 6,273,956. For example, in addition to the components described herein, embodiments of a dual-chamber processing system of the present invention can generally include: a plasma source with a switchable power supply, such as a microwave source or other suitable source; suitable robotic interfaces for loading and unloading wafers and performing other wafer-transfer steps; process gas sources; a venting system for bringing a chamber back to atmospheric pressure after a processing step is complete; and a pumping system for reducing the pressure within the chambers before and during wafer processing. According to one embodiment, the plasma source includes an individual remote plasma applicator associated with each of the chambers, such as a first plasma applicator 81 of a first chamber 60 and a second plasma applicator 82 of a second chamber 62 (Figure 2A). In the illustrated embodiment, the chambers 60,62 are each downstream of a plasma applicator 81,82. In an alternative embodiment, the plasma source is in situ (Figure 2B), wherein each chamber 60,62 is an in situ plasma reactor. Other additional components can also be used as desired.”